

Features

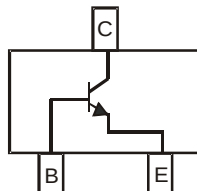
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complimentary PNP Type Available (DSS5320T)
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	5	A
Repetitive Peak Pulse Current (Note 3)	I_{CRP}	3	A
Continuous Collector Current	I_C	2	A
Base Current	I_B	0.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	209	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Operated under pulse conditions: Pulse width $\leq 100\text{ms}$, duty cycle ≤ 0.25 .
 4. Device mounted on FR-4 PCB; with minimum recommended pad layout.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 20V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	—	—	50	μA	V _{CB} = 20V, I _E = 0, T _A = 150°C
Collector-Base Breakdown Voltage	V _{(BR)CBO}	20	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	20	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	—	—	V	I _E = 100μA
ON CHARACTERISTICS (Note 5)						
DC Current Gain	h _{FE}	220	—	—	—	V _{CE} = 2V, I _C = 0.1A
		220	—	—		V _{CE} = 2V, I _C = 0.5A
		220	—	—		V _{CE} = 2V, I _C = 1A
		200	—	—		V _{CE} = 2V, I _C = 2A
		150	—	—		V _{CE} = 2V, I _C = 3A
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	70	mV	I _C = 0.5A, I _B = 50mA
		—	—	120		I _C = 1A, I _B = 50mA
		—	—	230		I _C = 2A, I _B = 40mA
		—	70	210		I _C = 2A, I _B = 200mA
		—	—	310		I _C = 3A, I _B = 300mA
Equivalent On-Resistance	R _{CE(SAT)}	—	35	105	mΩ	I _E = 2A, I _B = 200mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	1.1	V	I _C = 2A, I _B = 40mA
		—	—	1.2	V	I _C = 3A, I _B = 300mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	—	1.2	V	V _{CE} = 2V, I _C = 1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	—	—	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{ob}	—	—	35	pF	V _{CB} = 10V, f = 1MHz

Notes: 5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

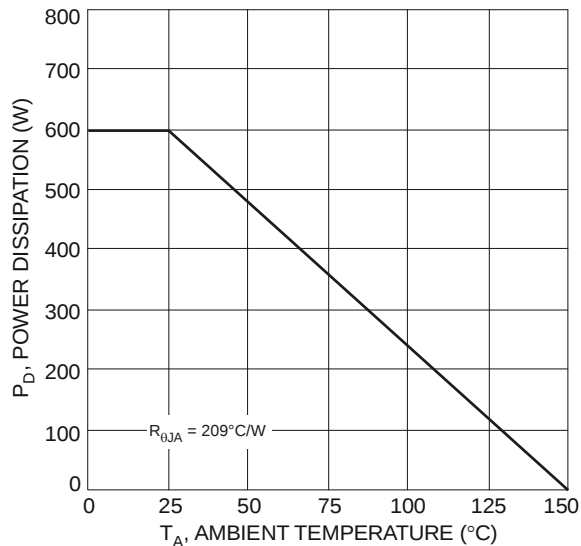


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 4)

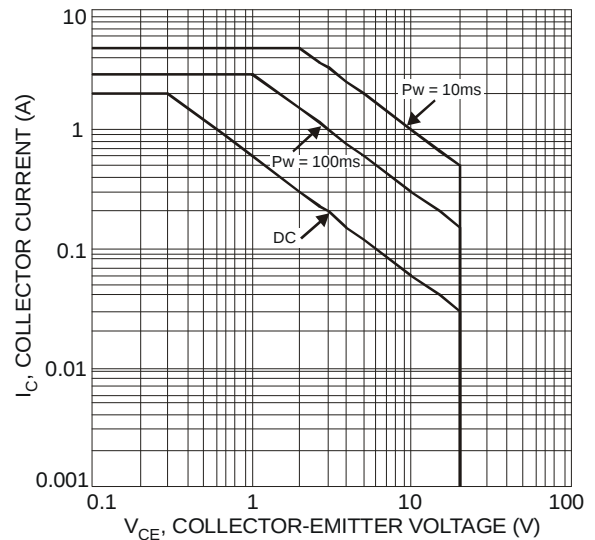


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

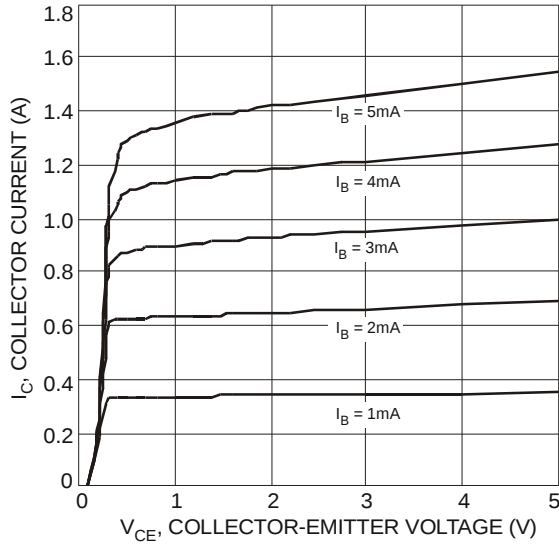


Fig. 3 Typical Collector Current vs. Collector-Emitter Voltage

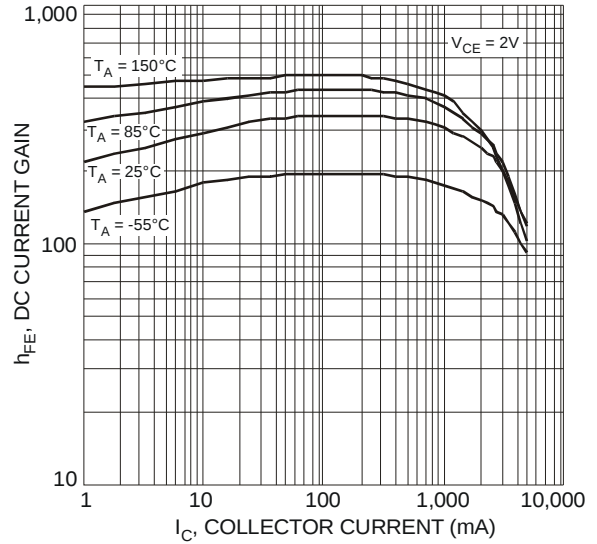


Fig. 4 Typical DC Current Gain vs. Collector Current

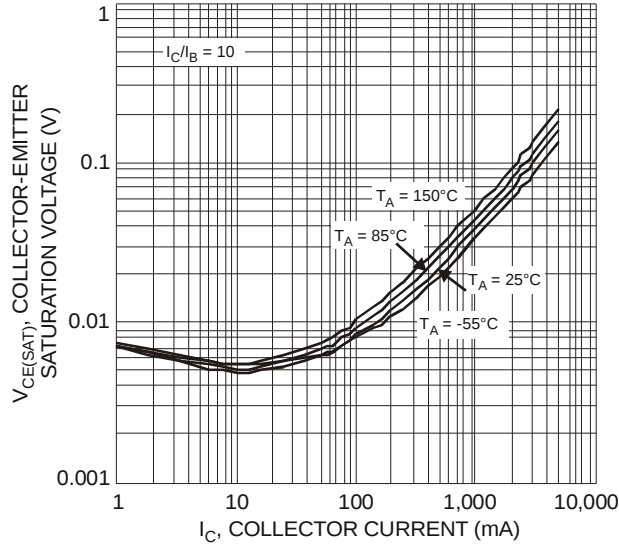


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

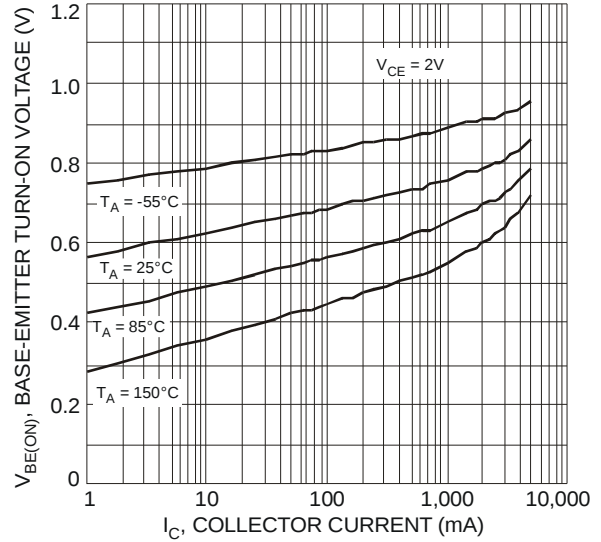


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

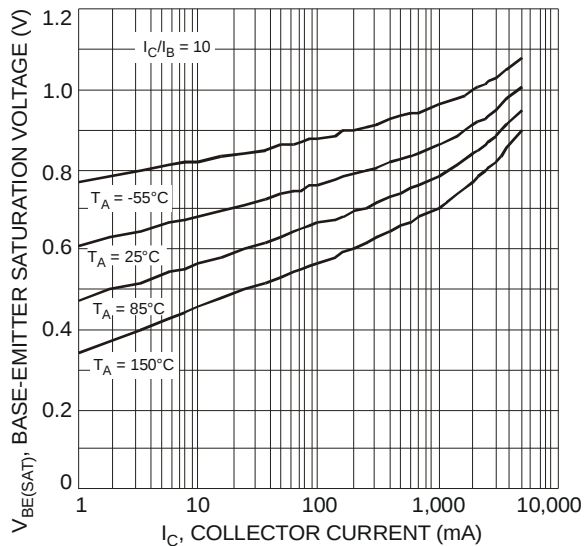


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

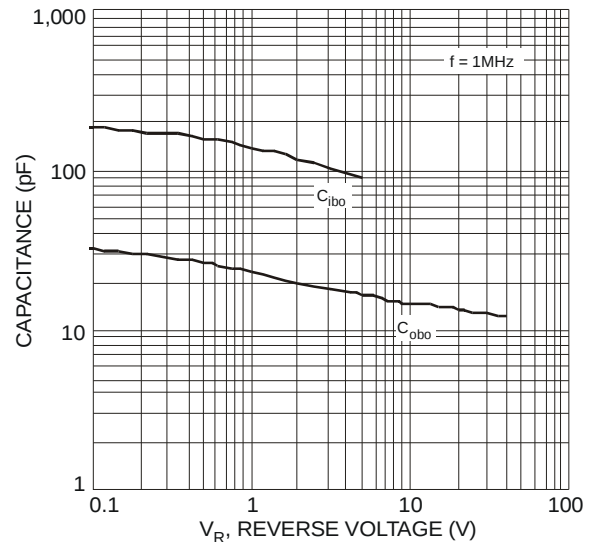


Fig. 8 Typical Capacitance Characteristics

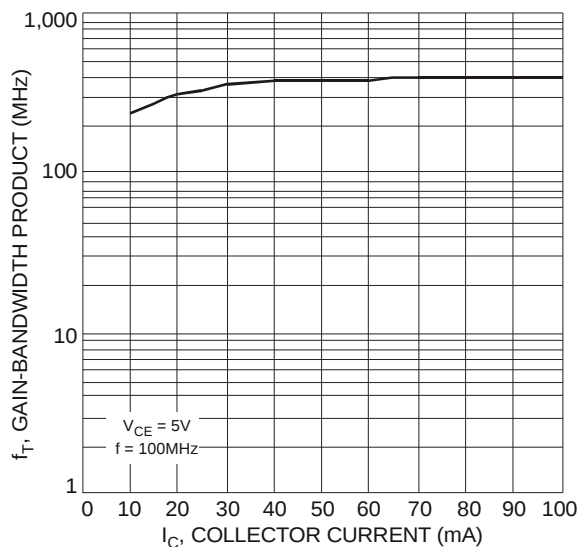


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

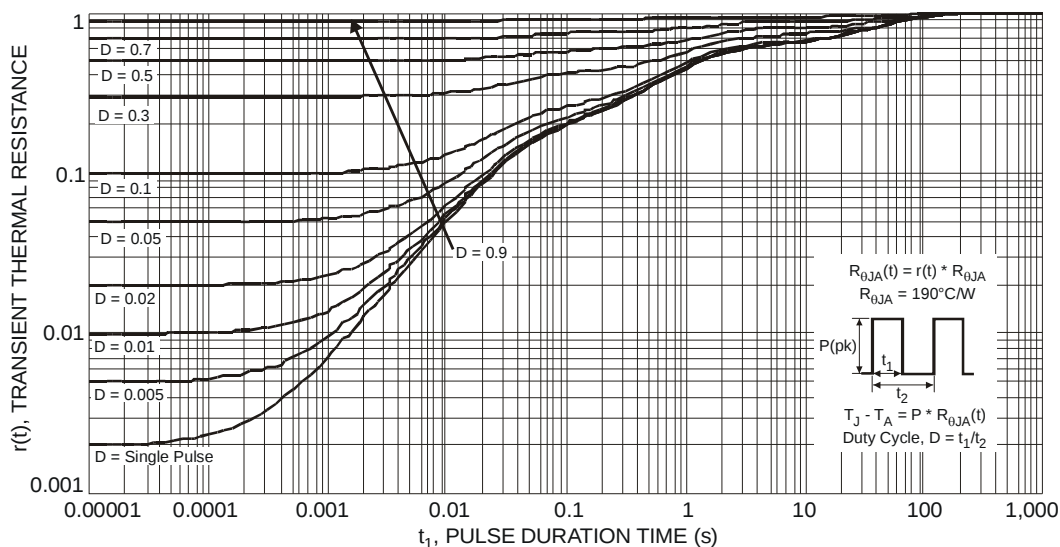


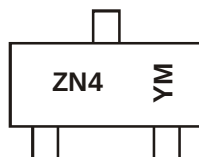
Fig. 10 Transient Thermal Response

Ordering Information (Note 6)

Part Number	Case	Packaging
DSS4320T-7	SOT-23	3000/Tape & Reel

 Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



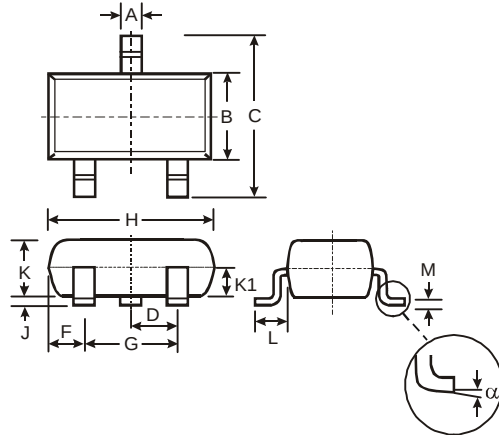
ZN4 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: V = 2008)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

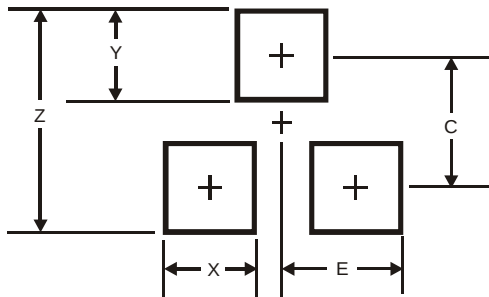
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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